



Pending

Active

- ☒ L1:(77) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "s...
- ☒ L2:(197925) Lee
- ☒ L3:(6) 1 and 2
- ☒ L4:(3372721) @ad<20011022
- ☒ L5:(5) 3 and 4
- ☒ L6:(3) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "si...
- ☒ L7:(918022) ratio or ratios
- ☒ L8:(3) 6 and 7
- ☒ L9:(18) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "s...
- ☒ L10:(17) 9 not 3
- ☒ L11:(13) 4 and 10
- ☒ L12:(11) 7 and 11
- ☒ L13:(1) ("6291030").PN.
- ☒ L14:(202774) etch\$
- ☒ L15:(1) 13 and 14
- ☒ L16:(296473) He or helium
- ☒ L17:(0) 13 and 16
- ☒ L18:(1) ("6211040").PN.
- ☒ L19:(0) 16 and 18
- ☒ L20:(5) 12 and 16
- ☒ L21:(66082) 438/\$7.ccls.
- ☒ L22:(117480) 257/\$7.ccls.
- ☒ L23:(138713) 21 or 22
- ☒ [REDACTED]

Failed

| Document ID | Issue Dat | Page | Title | Current O | Current XR | Retrieval | Inventor | SIC P |
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Ready

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| L Number | Hits | Search Text | DB | Time stamp |
|----------|---------|---|--------------------|---------------------|
| 1 | 77 | (SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios) | USPAT; US-PGPUB | 2003/06/07 20:56 |
| 2 | 197925 | Lee | USPAT; US-PGPUB | 2003/06/07 18:37 |
| 3 | 6 | ((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee | USPAT; US-PGPUB | 2003/06/07 18:38 |
| 4 | 3372721 | @ad<20011022 | USPAT; US-PGPUB | 2003/06/07 18:38 |
| 5 | 5 | ((((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee) and @ad<20011022 | USPAT; US-PGPUB | 2003/06/07 18:38 |
| 6 | 3 | (SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios) with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition") | USPAT; US-PGPUB | 2003/06/07 21:00 |
| 7 | 918022 | ratio or ratios | USPAT; US-PGPUB | 2003/06/07 19:29 |

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|---|----|--|--------------------|---------------------|
| 8 | 3 | ((SiO ₂ or "Si O ₂ " or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH ₄ " or "Si H ₄ " or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios) with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) and (ratio or ratios) | USPAT; US-PGPUB | 2003/06/07 19:29 |
| 9 | 18 | (SiO ₂ or "Si O ₂ " or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH ₄ " or "Si H ₄ " or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition") | USPAT; US-PGPUB | 2003/06/07 21:01 |

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|----|----|---|--------------------|---------------------|
| 10 | 17 | ((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee) | USPAT; US-PGPUB | 2003/06/07 21:01 |
| 11 | 13 | @ad<20011022 and (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee)) | USPAT; US-PGPUB | 2003/06/07 21:01 |

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|----|--------|---|--------------------|---------------------|
| 12 | 11 | (ratio or ratios) and (@ad<20011022 and (((SiO2 or "SiO2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "SiH4" or "SiH.sub.4" or "SiH.sub.4") with (HDP CVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition"))) not (((SiO2 or "SiO2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "SiH4" or "SiH.sub.4" or "SiH.sub.4") with (ratio or ratios)) and Lee))) | USPAT; US-PGPUB | 2003/06/07 21:47 |
| 13 | 1 | ("6291030").PN. | USPAT; US-PGPUB | 2003/06/07 21:47 |
| 14 | 202774 | etch\$ | USPAT; US-PGPUB | 2003/06/07 21:47 |
| 15 | 1 | ((("6291030").PN.) and etch\$ | USPAT; US-PGPUB | 2003/06/07 22:07 |
| 16 | 296473 | He or helium | USPAT; US-PGPUB | 2003/06/07 22:07 |
| 17 | 0 | ((("6291030").PN.) and (He or helium) | USPAT; US-PGPUB | 2003/06/07 22:08 |
| 18 | 1 | ("6211040").PN. | USPAT; US-PGPUB | 2003/06/07 22:08 |
| 19 | 0 | (He or helium) and ((("6211040").PN.) | USPAT; US-PGPUB | 2003/06/07 22:08 |

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|----|--------|--|--------------------|---------------------|
| 20 | 5 | ((ratio or ratios) and (@ad<20011022 and (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition"))) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lcc))) and (He or helium) | USPAT; US-PGPUB | 2003/06/07 22:22 |
| 21 | 66082 | 438/\$7.ccls. | USPAT; US-PGPUB | 2003/06/07 22:22 |
| 22 | 117480 | 257/\$7.ccls. | USPAT; US-PGPUB | 2003/06/07 22:23 |
| 23 | 138713 | 438/\$7.ccls. or 257/\$7.ccls. | USPAT; US-PGPUB | 2003/06/07 22:23 |
| 24 | 18 | ((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition"))) and (438/\$7.ccls. or 257/\$7.ccls.) | USPAT; US-PGPUB | 2003/06/07 22:23 |